

2N60

Power MOSFET

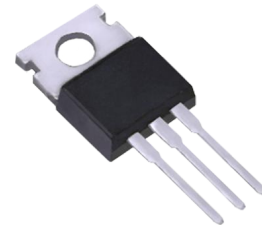
2A, 600V N-CHANNEL POWER MOSFET

■ DESCRIPTION

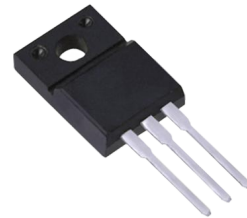
The UTC **2N60** is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

■ FEATURES

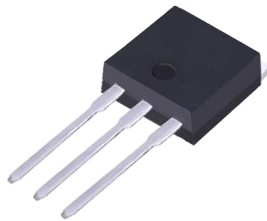
- * $R_{DS(ON)} < 5\Omega @ V_{GS} = 10V, I_D = 1A$
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness



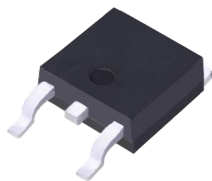
TO-220



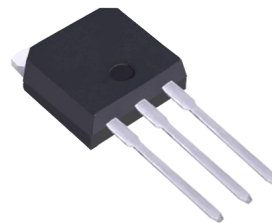
TO-220F



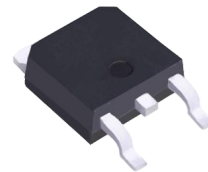
TO-262



TO-263



TO-251



TO-252

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT	
Drain-Source Voltage	V_{DSS}	600	V	
Gate-Source Voltage	V_{GSS}	± 30	V	
Avalanche Current (Note 2)	I_{AR}	2.0	A	
Drain Current	Continuous	I_D	2.0	A
	Pulsed (Note 2)	I_{DM}	8.0	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	140	mJ
	Repetitive (Note 2)	E_{AR}	4.5	mJ
Peak Diode Recovery dv/dt (Note 4)	dv/dt	4.5	V/ns	
Power Dissipation ($T_C = 25^\circ\text{C}$)	TO-220/ TO-262	P_D	54	W
	TO-220F/TO-220F1 TO-220F3		23	W
	TO-220F2		24	W
	TO-251/TO-251L TO-251S/TO-251S2 TO-251S4/TO-252 TO-252D		44	W
	TO-126/TO-126C		40	W
	DFN5060-8		22	W
	Junction Temperature		T_J	+150
Operating Temperature	T_{OPR}	-55 ~ +150	$^\circ\text{C}$	
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by T_J .

3. $L=64\text{mH}$, $I_{AS}=2.0\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD}\leq 2.4\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	PACKAGE	SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2 TO-220F3/TO-262	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-251/TO-251L TO-251S/TO-251S2 TO-251S4/TO-252 TO-252D		100	$^\circ\text{C}/\text{W}$
	TO-126/TO-126C		89	$^\circ\text{C}/\text{W}$
	DFN5060-8		75	$^\circ\text{C}/\text{W}$
	TO-220/ TO-262		2.32	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1 TO-220F3		5.5	$^\circ\text{C}/\text{W}$
	TO-220F2		5.43	$^\circ\text{C}/\text{W}$
Junction to Case	TO-251/TO-251L TO-251S/TO-251S2 TO-251S4/TO-252 TO-252D	θ_{JC}	2.87	$^\circ\text{C}/\text{W}$
	TO-126/TO-126C		3.12	$^\circ\text{C}/\text{W}$
	DFN5060-8		5.6	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	600			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 600V, V_{GS} = 0V$			10	μA
		$V_{DS} = 480V, T_C = 125^\circ\text{C}$			100	μA
Gate-Source Leakage Current	Forward	I_{GSS}			100	nA
	Reverse					
		$V_{GS} = -30V, V_{DS} = 0V$			-100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D=250\mu A$, Referenced to 25°C		0.4		$V/^\circ\text{C}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 1A$		3.6	5	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1\text{MHz}$		300	350	pF
Output Capacitance	C_{OSS}			45	50	pF
Reverse Transfer Capacitance	C_{RSS}			10	13	pF
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q_G	$V_{DS}=480V, V_{GS}=10V,$ $I_D=2.4A$ (Note 1, 2)		40	50	nC
Gate-Source Charge	Q_{GS}			4.2		nC
Gate-Drain Charge	Q_{GD}			8.4		nC
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD} = 300V, I_D = 2.4A,$ $R_G = 25\Omega$ (Note 1, 2)		40	60	ns
Turn-On Rise Time	t_R			35	55	ns
Turn-Off Delay Time	$t_{D(OFF)}$			90	120	ns
Turn-Off Fall Time	t_F			50	60	ns
DRAIN-SOURCE DIODE CHARACTERISTICS						
Continuous Drain-Source Current	I_S				2.0	A
Pulsed Drain-Source Current	I_{SM}				8.0	A
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_{SD} = 2.0A$			1.4	V
Reverse Recovery Time	t_{rr}	$V_{GS} = 0V, I_{SD} = 2.4A,$ $di/dt = 100A/\mu s$ (Note 1)		180		ns
Reverse Recovery Charge	Q_{rr}			0.72		μC

Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TYPICAL CHARACTERISTICS

